Effect of internal radiation on the crystal-melt interface shape in Czochralski oxide growth

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Introduction.

Most oxide crystals (BGO, BSO, BTO, YAG, GGG) display transparency to infrared radiation that can greatly influence the crystal-melt interface shape during Czochralski growth since an additional mechanism arises for a heat removal from the vicinity of the crystallization front. Additional important factor affecting the shape of solid/liquid interface is related to the Fresnel's reflection (refraction) at the transparent crystal surface [1].

- The shape of real crystals can be appreciably differed from a regular cylinder or a cone that has to lead to scattering of radiation at the crystal surface and, consequently, to smoothing of the radiation heat flux distribution at the melt/solid interface.
- Many oxide crystals demonstrate the pronounced tendency toward faceting of the solidification front that imply considerable supercooling at the facetted interface which should be taken into account in global simulation.

Note:

Up to now numerical calculation of facet formation was performed only for Bridgman process and internal radiation transport was treated using either the Rosseland diffusion approximation [2] or P_1 -approximation [3]

The objectives of the modeling:

- 1. To investigate the influence of deflections in the shape of a real crystal from conical and cylindrical geometry on the distributions of radiative heat flux over the crystallization front.
- 2. To investigate the effect of internal radiation and Fresnel reflection at the crystal surface on the process of facet formation in Cz oxides growth.

As a representative growth process, the $Bi_4Ge_3O_{12}$ low-thermal gradients Cz growth was considered (see Fig.A).



In this case a single parameter is needed (with the exception of crystallographic orientation of the facet) to define the position of the facet on the crystallization front and its size. In suggested algorithm the value of parameter

-90

05 10 15 20 25 30 35

Described approach is a numerical expansion of the analytical one suggested in [5].







the axis of symmetry in the crystal for different values of <u>ATmax</u>: 1 – 0 K f ΔTmax: · 3 - 0.8K

Calculation of RCT problem inside the crystal and gas gap above the melt (domains 1, 2). Boundary conditions at

if r=0

the interface are of the first kind:

 $T_L = T_m - \Delta T_{\max}$



0.9







